

FIELD EFFECT TRANSISTOR**ABSTRACT**

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A field effect transistor includes a substrate having a doping of a first conductivity type, a drain area in the substrate having a doping of a second conductivity type opposite the first conductivity type, a source area in the substrate being laterally spaced from the drain area and having a doping of the second conductivity type, and a channel area in the substrate that is arranged between the source area and the drain area. In a portion of the substrate bordering the drain area, an area having a doping of the second conductivity type, which is connected to the drain area, is arranged such that in the portion alternating regions having the first conductivity type and having the second conductivity type are arranged.

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